



Welcome to [E-XFL.COM](https://www.e-xfl.com)

### **Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems**

**Embedded - System On Chip (SoC)** refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

### **What are Embedded - System On Chip (SoC)?**

**System On Chip (SoC)** integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

#### **Details**

Product Status	Active
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	512KB
RAM Size	64KB
Peripherals	DDR, PCIe, SERDES
Connectivity	CANbus, Ethernet, I <sup>2</sup> C, SPI, UART/USART, USB
Speed	166MHz
Primary Attributes	FPGA - 150K Logic Modules
Operating Temperature	-40°C ~ 100°C (Tj)
Package / Case	484-BFBGA
Supplier Device Package	484-FBGA (19x19)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/m2s150t-fcv484i">https://www.e-xfl.com/product-detail/microchip-technology/m2s150t-fcv484i</a>



**Power Matters.™**

**Microsemi Corporate Headquarters**

One Enterprise, Aliso Viejo,  
CA 92656 USA

Within the USA: +1 (800) 713-4113

Outside the USA: +1 (949) 380-6100

Fax: +1 (949) 215-4996

Email: [sales.support@microsemi.com](mailto:sales.support@microsemi.com)

[www.microsemi.com](http://www.microsemi.com)

© 2016 Microsemi Corporation. All rights reserved. Microsemi and the Microsemi logo are trademarks of Microsemi Corporation. All other trademarks and service marks are the property of their respective owners.

Microsemi makes no warranty, representation, or guarantee regarding the information contained herein or the suitability of its products and services for any particular purpose, nor does Microsemi assume any liability whatsoever arising out of the application or use of any product or circuit. The products sold hereunder and any other products sold by Microsemi have been subject to limited testing and should not be used in conjunction with mission-critical equipment or applications. Any performance specifications are believed to be reliable but are not verified, and Buyer must conduct and complete all performance and other testing of the products, alone and together with, or installed in, any end-products. Buyer shall not rely on any data and performance specifications or parameters provided by Microsemi. It is the Buyer's responsibility to independently determine suitability of any products and to test and verify the same. The information provided by Microsemi hereunder is provided "as is, where is" and with all faults, and the entire risk associated with such information is entirely with the Buyer. Microsemi does not grant, explicitly or implicitly, to any party any patent rights, licenses, or any other IP rights, whether with regard to such information itself or anything described by such information. Information provided in this document is proprietary to Microsemi, and Microsemi reserves the right to make any changes to the information in this document or to any products and services at any time without notice.

**About Microsemi**

Microsemi Corporation (Nasdaq: MSCC) offers a comprehensive portfolio of semiconductor and system solutions for aerospace & defense, communications, data center and industrial markets. Products include high-performance and radiation-hardened analog mixed-signal integrated circuits, FPGAs, SoCs and ASICs; power management products; timing and synchronization devices and precise time solutions, setting the world's standard for time; voice processing devices; RF solutions; discrete components; enterprise storage and communication solutions, security technologies and scalable anti-tamper products; Ethernet solutions; Power-over-Ethernet ICs and midspans; as well as custom design capabilities and services. Microsemi is headquartered in Aliso Viejo, California, and has approximately 4,800 employees globally. Learn more at [www.microsemi.com](http://www.microsemi.com).

- Added [Table 244](#), page 94 and [Table 256](#), page 99 (SAR 73971).
- Updated the [SerDes Electrical and Timing AC and DC Characteristics](#), page 121 (SAR 71171).
- Added the [DEVRST\\_N Characteristics](#), page 116 (SAR 64100, 72103).
- Added [Table 298](#), page 122 (SAR 71897).
- Updated [Table 25](#), page 22, [Table 26](#), page 23, and [Table 27](#), page 23 (SAR 74570).
- Added 060 devices in [Table 277](#), page 107, [Table 278](#), page 108, and [Table 279](#), page 108 (SAR 57898).
- Updated duty cycle parameter of crystal in [Table 280](#), page 109 and [Table 281](#), page 109 (SAR 57898).
- Added 32 KHz mode PLL acquisition time in [Table 282](#), page 110 (SAR 68281).
- Updated [Table 293](#), page 119 for 060 devices (SAR 57828).
- Updated [Table 297](#), page 122 for CID value (SAR 70878).

## 1.4 Revision 8.0

The following is a summary of the changes in revision 8.0 of this document.

- Updated [Table 11](#), page 12 (SAR 69218).
- Updated [Table 12](#), page 13 (SAR 69218).
- Updated [Table 283](#), page 111 (SAR 69000).

## 1.5 Revision 7.0

The following is a summary of the changes in revision 7.0 of this document.

- Updated [Table 1](#), page 4(SAR 68620).

## 1.6 Revision 6.0

The following is a summary of the changes in revision 6.0 of this document.

- Updated [Table 5](#), page 7 (SAR 65949).
- Updated [Table 9](#), page 10 (SAR 62995).
- Updated [Table 123](#), page 47 and [Table 133](#), page 49 (SAR 67210).
- Added [Embedded NVM \(eNVM\) Characteristics](#), page 104 (SAR 52509).
- Updated [Table 277](#), page 107 (SAR 64855).
- Updated [Table 282](#), page 110 (SAR 65958 and SAR 56666).
- Added [DDR Memory Interface Characteristics](#), page 120 (SAR 66223).
- Added [SFP Transceiver Characteristics](#), page 120 (SAR 63105).
- Updated [Table 302](#), page 123 and [Table 309](#), page 129 (SAR 66314).

## 1.7 Revision 5.0

The following is a summary of the changes in revision 5.0 of this document.

- Updated [Table 1](#), page 4.
- Updated [Table 4](#), page 6 for  $T_J$  symbol information.
- Updated [Table 5](#), page 7 (SAR 63109).
- Updated [Table 9](#), page 10.
- Updated [Table 282](#), page 110 (SAR 62012).
- Added [Table 290](#), page 116 (SAR 64100).
- Added [Table 306](#), page 128, [Table 307](#), page 128 (SAR 50424).

## 1.8 Revision 4.0

The following is a summary of the changes in revision 4.0 of this document.

- Updated [Table 1](#), page 4. Changed the Status of 090 devices to "Production" (SAR 62750).
- Updated [Figure 10](#), page 70. Removed inverter bubble from DDR\_IN latch (SAR 61418).
- Updated [SerDes Electrical and Timing AC and DC Characteristics](#), page 121 (SAR 62836).

**Table 11 • SmartFusion2 and IGLOO2 Quiescent Supply Current ( $V_{DD} = 1.2\text{ V}$ ) – Typical Process**

Symbol	Modes	005	010	025	050	060	090	150	Unit	Conditions
IDC2	Flash*Freeze	1.4	2.6	3.7	5.1	5.0	5.1	8.9	mA	Typical ( $T_J = 25\text{ }^\circ\text{C}$ )
		12.0	20.0	26.6	35.3	35.4	35.7	57.8	mA	Commercial ( $T_J = 85\text{ }^\circ\text{C}$ )
		18.5	30.8	41.0	54.5	54.5	55.0	89.0	mA	Industrial ( $T_J = 100\text{ }^\circ\text{C}$ )

**Table 12 • SmartFusion2 and IGLOO2 Quiescent Supply Current ( $V_{DD} = 1.26\text{ V}$ ) – Worst-Case Process**

Symbol	Modes	005	010	025	050	060	090	150	Unit	Conditions
IDC1	Non-Flash*Freeze	43.8	57.0	84.6	132.3	161.4	163.0	242.5	mA	Commercial ( $T_J = 85\text{ }^\circ\text{C}$ )
		65.3	85.7	127.8	200.9	245.4	247.8	369.0	mA	Industrial ( $T_J = 100\text{ }^\circ\text{C}$ )
IDC2	Flash*Freeze	29.1	45.6	51.7	62.7	69.3	70.0	84.8	mA	Commercial ( $T_J = 85\text{ }^\circ\text{C}$ )
		44.9	70.3	79.7	96.5	106.8	107.8	130.6	mA	Industrial ( $T_J = 100\text{ }^\circ\text{C}$ )

### 2.3.2.2 Programming Currents

The following tables represent programming, verify and Inrush currents for SmartFusion2 SoC and IGLOO2 FPGA devices.

**Table 13 • Currents During Program Cycle,  $0\text{ }^\circ\text{C} \leq T_J \leq 85\text{ }^\circ\text{C}$  – Typical Process**

Power Supplies	Voltage (V)	005	010	025	050	060	090	150 <sup>1</sup>	Unit
$V_{DD}$	1.26	46	53	55	58	30	42	52	mA
$V_{PP}$	3.46	8	11	6	10	9	12	12	mA
$V_{PPNVM}$	3.46	1	2	2	3	3	3		mA
$V_{DDI}$	2.62	31	16	17	1	12	12	81	mA
	3.46	62	31	36	1	12	17	84	mA
Number of banks		7	8	8	10	10	9	19	

1.  $V_{PP}$  and  $V_{PPNVM}$  are internally shorted.

**Table 14 • Currents During Verify Cycle,  $0\text{ }^\circ\text{C} \leq T_J \leq 85\text{ }^\circ\text{C}$  – Typical Process**

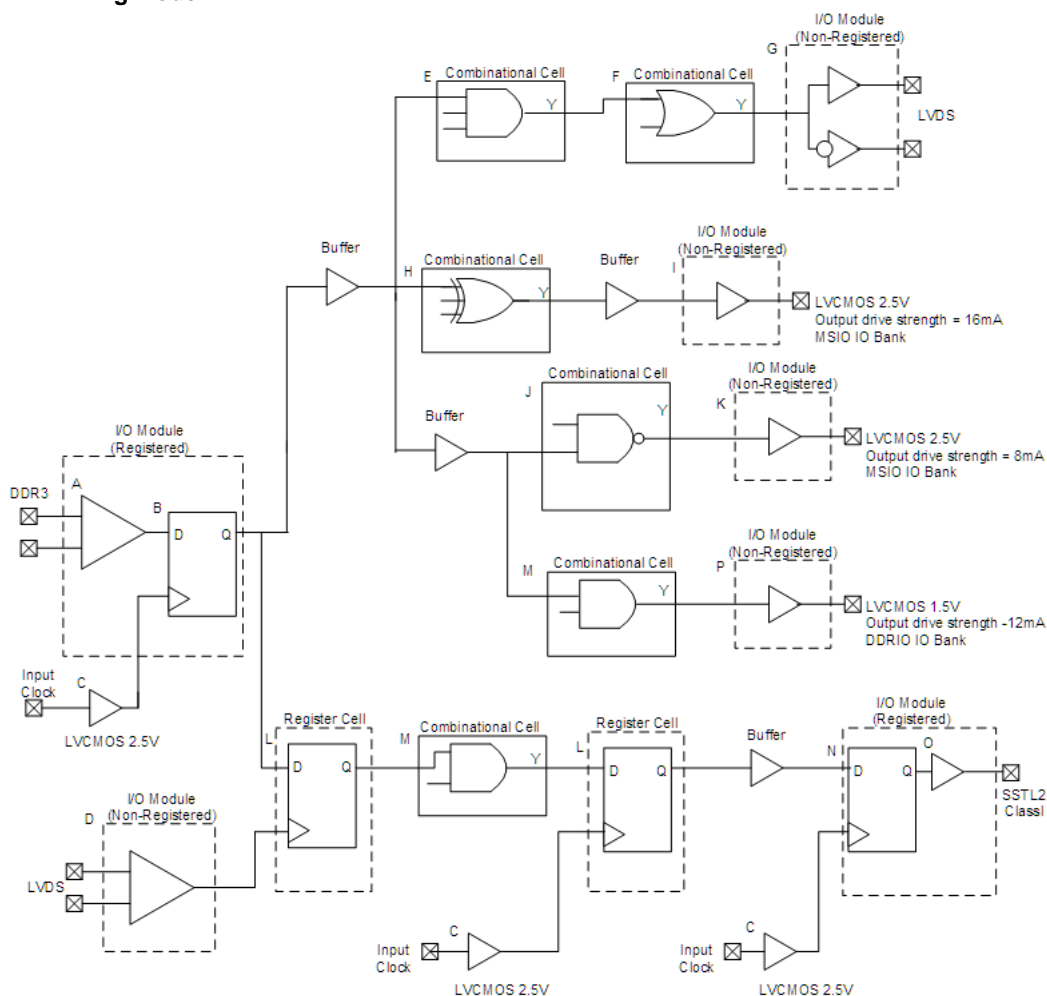
Power Supplies	Voltage (V)	005	010	025	050	060	090	150 <sup>1</sup>	Unit
$V_{DD}$	1.26	44	53	55	58	33	41	51	mA
$V_{PP}$	3.46	6	5	3	15	8	11	12	mA
$V_{PPNVM}$	3.46	1	0	0	1	1	1		mA
$V_{DDI}$	2.62	31	16	17	1	12	11	81	mA
	3.46	61	32	36	1	12	17	84	mA
Number of banks		7	8	8	10	10	9	19	

1.  $V_{PP}$  and  $V_{PPNVM}$  are internally shorted.

### 2.3.4 Timing Model

This section describes timing model and timing parameters.

Figure 2 • Timing Model



The following table lists the timing model parameters in worst commercial-case conditions when  $T_J = 85^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

Table 17 • Timing Model Parameters

Index	Symbol	Description	-1	Unit	For More Information
A	$T_{PY}$	Propagation delay of DDR3 receiver	1.605	ns	See Table 137, page 50
B	$T_{ICLKQ}$	Clock-to-Q of the input data register	0.16	ns	See Table 221, page 71
		Setup time of the input data register	0.357	ns	See Table 221, page 71
C	$T_{RCKH}$	Input high delay for global clock	1.53	ns	See Table 227, page 78
		Input low delay for global clock	0.897	ns	See Table 227, page 78
D	$T_{PY}$	Input propagation delay of LVDS receiver	2.774	ns	See Table 167, page 56
E	$T_{DP}$	Propagation delay of a three-input AND gate	0.198	ns	See Table 223, page 76

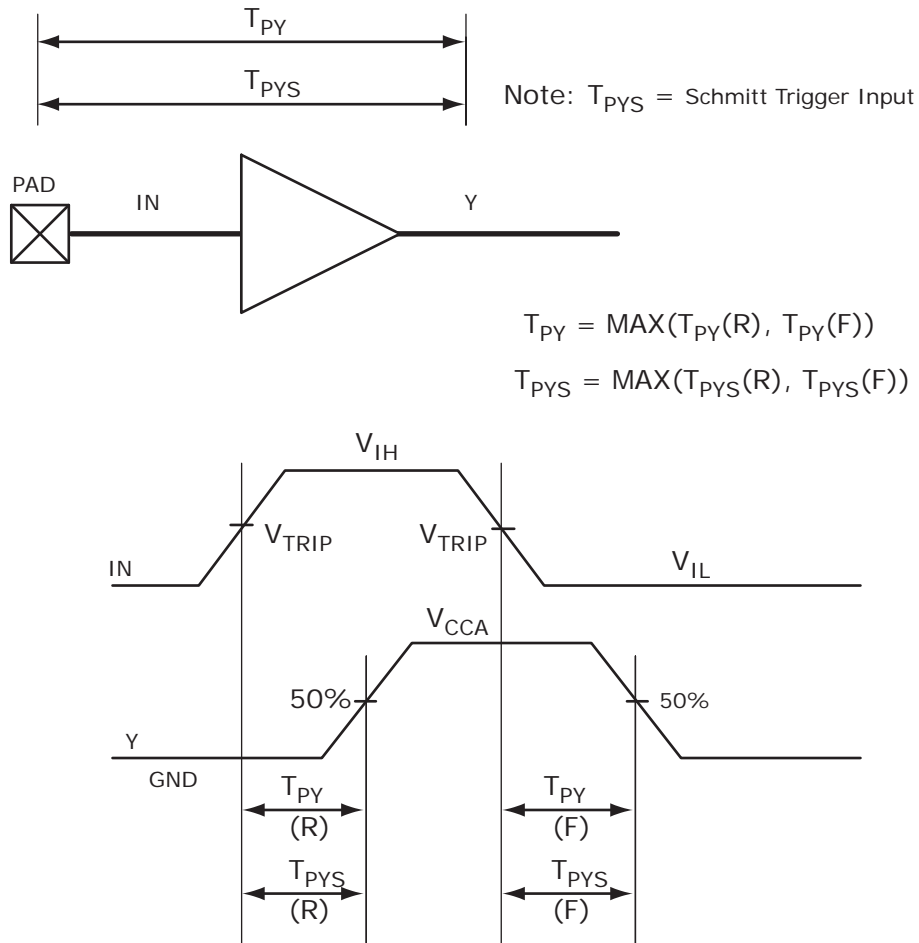
## 2.3.5 User I/O Characteristics

There are three types of I/Os supported in the IGLOO2 FPGA and SmartFusion2 SoC FPGA families: MSIO, MSIOD, and DDRIO I/O banks. The I/O standards supported by the different I/O banks is described in the I/Os section of the *UG0445: IGLOO2 FPGA and SmartFusion2 SoC FPGA Fabric User Guide*.

### 2.3.5.1 Input Buffer and AC Loading

The following figure shows the input buffer and AC loading.

**Figure 3 • Input Buffer AC Loading**



**Table 22 • Maximum Frequency Summary Table for Voltage-Referenced I/O in Worst-Case Industrial Conditions**

I/O	MSIO	MSIOD	DDRIO	Unit
LPDDR			200	MHz
HSTL1.5 V			200	MHz
SSTL 2.5 V	255	350	200	MHz
SSTL 1.8 V			334	MHz
SSTL 1.5 V			334	MHz

**Table 23 • Maximum Frequency Summary Table for Differential I/O in Worst-Case Industrial Conditions**

I/O	MSIO	MSIOD	Unit
LVPECL (input only)	450		MHz
LVDS 3.3 V	267.5		MHz
LVDS 2.5 V	267.5	350	MHz
RSDS	260	350	MHz
BLVDS	250		MHz
MLVDS	250		MHz
Mini-LVDS	260	350	MHz

**Table 100 • HSTL AC Test Parameter Specification**

Parameter	Symbol	Typ	Unit
Measuring/trip point for data path	$V_{TRIP}$	0.75	V
Resistance for enable path ( $T_{ZH}$ , $T_{ZL}$ , $T_{HZ}$ , $T_{LZ}$ )	$R_{ENT}$	2K	$\Omega$
Capacitive loading for enable path ( $T_{ZH}$ , $T_{ZL}$ , $T_{HZ}$ , $T_{LZ}$ )	$C_{ENT}$	5	pF
Reference resistance for data test path for HSTL15 Class I ( $T_{DP}$ )	$RTT\_TEST$	50	$\Omega$
Reference resistance for data test path for HSTL15 Class II ( $T_{DP}$ )	$RTT\_TEST$	25	$\Omega$
Capacitive loading for data path ( $T_{DP}$ )	$C_{LOAD}$	5	pF

**AC Switching Characteristics**

Worst-case commercial conditions:  $T_J = 85\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ , worst-case  $V_{DDI}$ .

**Table 101 • HSTL Receiver Characteristics for DDRIO I/O Bank with Fixed Code (Input Buffers)**

		$T_{PY}$		
On-Die Termination (ODT)		-1	-Std	Unit
Pseudo differential	None	1.605	1.888	ns
	47.8	1.614	1.898	ns
True differential	None	1.622	1.909	ns
	47.8	1.628	1.916	ns

**Table 102 • HSTL Transmitter Characteristics for DDRIO I/O Bank (Output and Tristate Buffers)**

	$T_{DP}$		$T_{ZL}$		$T_{ZH}$		$T_{HZ}$		$T_{LZ}$		Unit
	-1	-Std	-1	-Std	-1	-Std	-1	-Std	-1	-Std	
<b>HSTL Class I</b>											
Single-ended	2.6	3.059	2.514	2.958	2.514	2.958	2.431	2.86	2.431	2.86	ns
Differential	2.621	3.083	2.648	3.115	2.647	3.113	2.925	3.442	2.923	3.44	ns
<b>HSTL Class II</b>											
Single-ended	2.511	2.954	2.488	2.927	2.49	2.93	2.409	2.833	2.411	2.836	ns
Differential	2.528	2.974	2.552	3.003	2.551	3.001	2.897	3.409	2.896	3.408	ns

**2.3.6.2 Stub-Series Terminated Logic**

Stub-Series Terminated Logic (SSTL) for 2.5 V (SSTL2), 1.8 V (SSTL18), and 1.5 V (SSTL15) is supported in IGLOO2 and SmartFusion2 SoC FPGAs. SSTL2 is defined by JEDEC standard JESD8-9B and SSTL18 is defined by JEDEC standard JESD8-15. IGLOO2 SSTL I/O configurations are designed to meet double data rate standards DDR/2/3 for general purpose memory buses. Double data rate standards are designed to meet their JEDEC specifications as defined by JEDEC standard JESD79F for DDR, JEDEC standard JESD79-2F for DDR, JEDEC standard JESD79-3D for DDR3, and JEDEC standard JESD209A for LPDDR.



**Table 191 • M-LVDS AC Switching Characteristics for Receiver (for MSIOD I/O Bank - Input Buffers)**

On-Die Termination (ODT)	$T_{PY}$		Unit
	-1	-Std	
None	2.495	2.934	ns
100	2.495	2.935	ns

**Table 192 • M-LVDS AC Switching Characteristics for Transmitter (for MSIO I/O Bank - Output and Tristate Buffers)**

$T_{DP}$		$T_{ZL}$		$T_{ZH}$		$T_{HZ}$		$T_{LZ}$		Unit
-1	-Std	-1	-Std	-1	-Std	-1	-Std	-1	-Std	
2.258	2.656	2.348	2.762	2.334	2.746	2.123	2.497	2.125	2.5	ns

### 2.3.7.4 Mini-LVDS

Mini-LVDS is an unidirectional interface from the timing controller to the column drivers and is designed to the Texas Instruments Standard SLDA007A.

#### Mini-LVDS Minimum and Maximum Input and Output Levels

**Table 193 • Mini-LVDS Recommended DC Operating Conditions**

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	$V_{DDI}$	2.375	2.5	2.625	V

**Table 194 • Mini-LVDS DC Input Voltage Specification**

Parameter	Symbol	Min	Max	Unit
DC Input voltage	$V_I$	0	2.925	V

**Table 195 • Mini-LVDS DC Output Voltage Specification**

Parameter	Symbol	Min	Typ	Max	Unit
DC output logic high	$V_{OH}$	1.25	1.425	1.6	V
DC output logic low	$V_{OL}$	0.9	1.075	1.25	V

**Table 196 • Mini-LVDS DC Differential Voltage Specification**

Parameter	Symbol	Min	Max	Unit
Differential output voltage swing	$V_{OD}$	300	600	mV
Output common mode voltage	$V_{OCM}$	1	1.4	V
Input common mode voltage	$V_{ICM}$	0.3	1.2	V
Input differential voltage	$V_{ID}$	100	600	mV

**Table 197 • Mini-LVDS Minimum and Maximum AC Switching Speed**

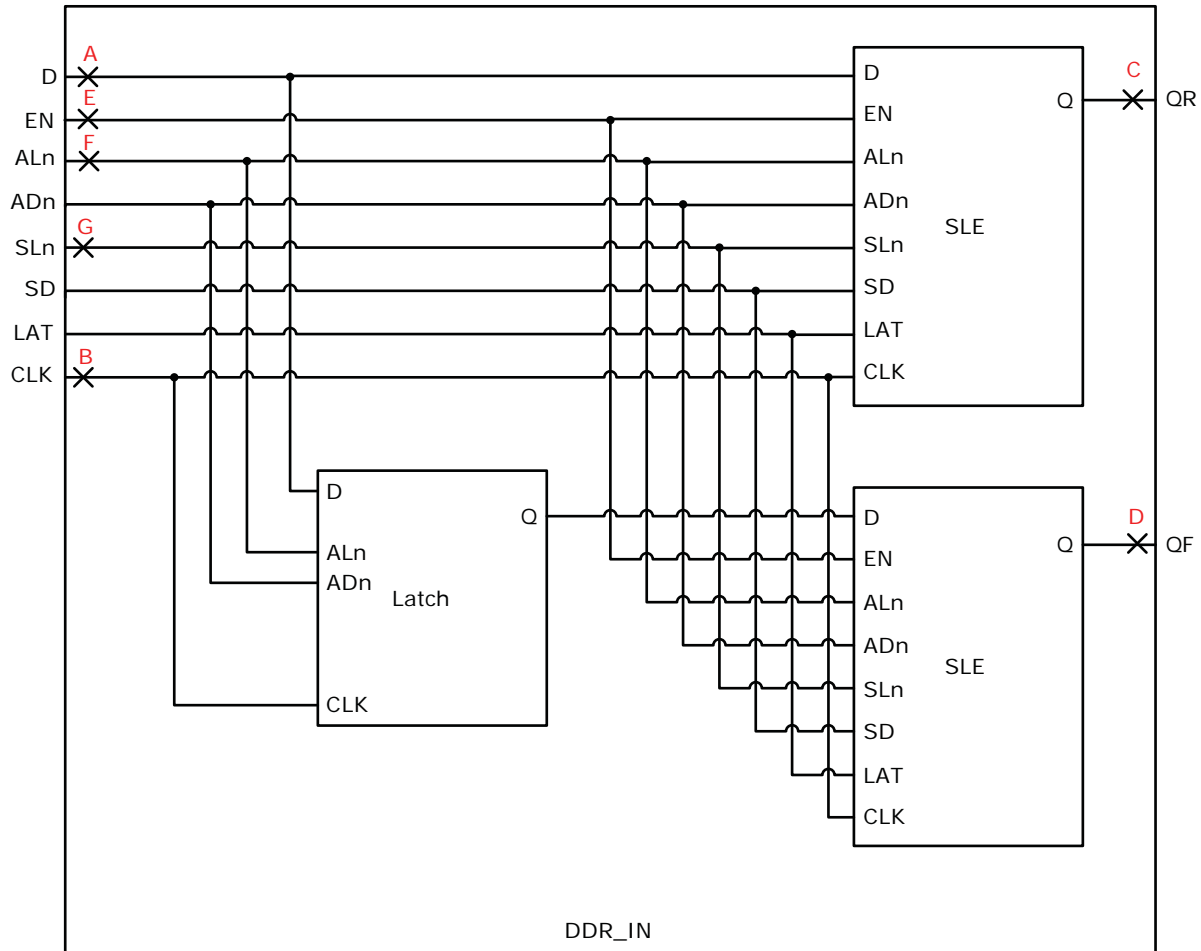
Parameter	Symbol	Max	Unit	Conditions
Maximum data rate (for MSIO I/O bank)	$D_{MAX}$	520	Mbps	AC loading: 2 pF / 100 $\Omega$ differential load
Maximum data rate (for MSIOD I/O bank)	$D_{MAX}$	700	Mbps	AC loading: 2 pF / 100 $\Omega$ differential load

### 2.3.9 DDR Module Specification

This section describes input and output DDR module and timing specifications.

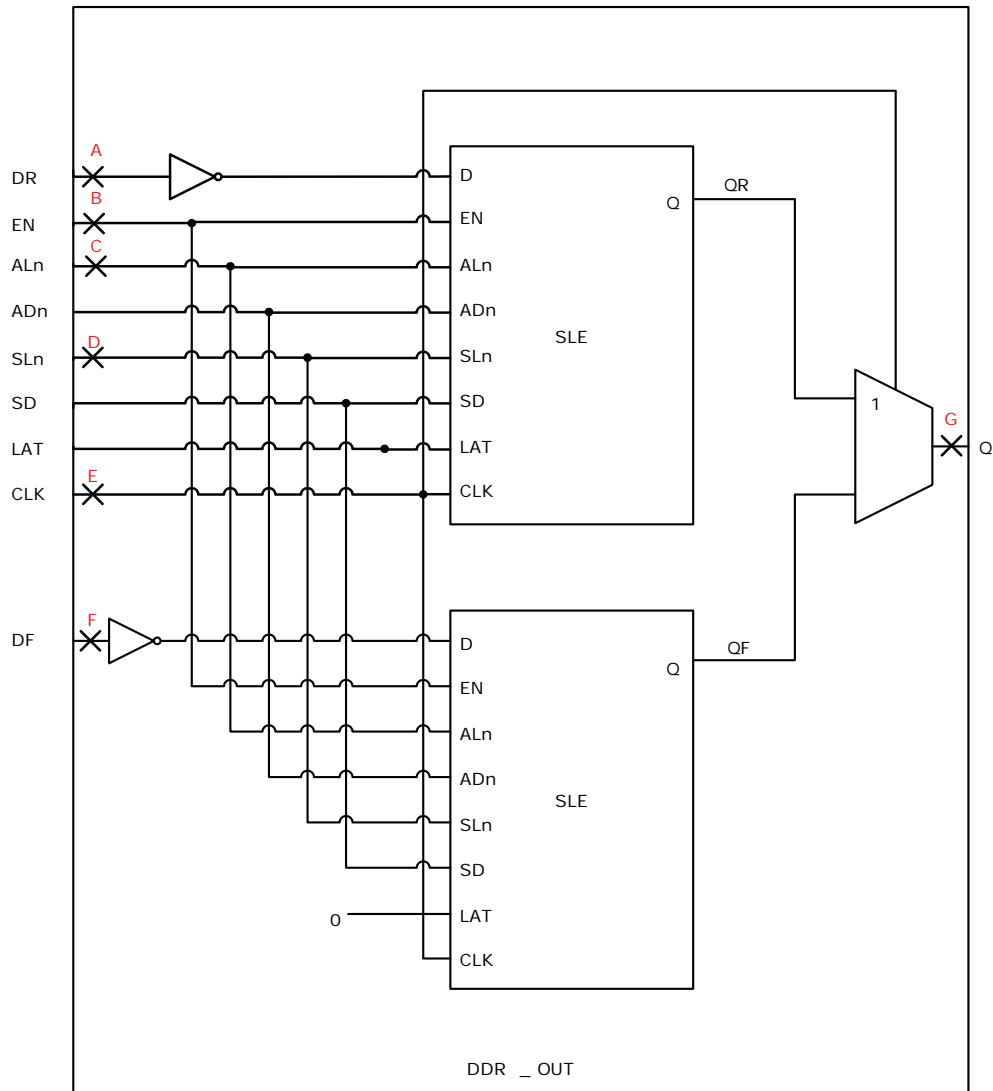
#### 2.3.9.1 Input DDR Module

Figure 10 • Input DDR Module



**2.3.9.4 Output DDR Module**

**Figure 12 • Output DDR Module**



## 2.3.11 Global Resource Characteristics

The IGLOO2 and SmartFusion2 SoC FPGA devices offer a powerful, low skew global routing network which provides an effective clock distribution throughout the FPGA fabric. See [UG0445: IGLOO2 FPGA and SmartFusion2 SoC FPGA Fabric User Guide](#) for the positions of various global routing resources.

The following table lists the 150 device global resources in worst commercial-case conditions when  $T_J = 85\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 225 • 150 Device Global Resource**

Parameter	Symbol	-1		-Std		Unit
		Min	Max	Min	Max	
Input low delay for global clock	$T_{RCKL}$	0.83	0.911	0.831	0.913	ns
Input high delay for global clock	$T_{RCKH}$	1.457	1.588	1.715	1.869	ns
Maximum skew for global clock	$T_{RCKSW}$		0.131		0.154	ns

The following table lists the 090 device global resources in worst commercial-case conditions when  $T_J = 85\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 226 • 090 Device Global Resource**

Parameter	Symbol	-1		-Std		Unit
		Min	Max	Min	Max	
Input low delay for global clock	$T_{RCKL}$	0.835	0.888	0.833	0.886	ns
Input high delay for global clock	$T_{RCKH}$	1.405	1.489	1.654	1.752	ns
Maximum skew for global clock	$T_{RCKSW}$		0.084		0.098	ns

The following table lists the 050 device global resources in worst commercial-case conditions when  $T_J = 85\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 227 • 050 Device Global Resource**

Parameter	Symbol	-1		-Std		Unit
		Min	Max	Min	Max	
Input low delay for global clock	$T_{RCKL}$	0.827	0.897	0.826	0.896	ns
Input high delay for global clock	$T_{RCKH}$	1.419	1.53	1.671	1.8	ns
Maximum skew for global clock	$T_{RCKSW}$		0.111		0.129	ns

The following table lists the 025 device global resources in worst commercial-case conditions when  $T_J = 85\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 228 • 025 Device Global Resource**

Parameter	Symbol	-1		-Std		Unit
		Min	Max	Min	Max	
Input low delay for global clock	$T_{RCKL}$	0.747	0.799	0.745	0.797	ns
Input high delay for global clock	$T_{RCKH}$	1.294	1.378	1.522	1.621	ns
Maximum skew for global clock	$T_{RCKSW}$		0.084		0.099	ns

**Table 232 • RAM1K18 – Dual-Port Mode for Depth × Width Configuration 2K × 9 (continued)**

Parameter	Symbol	–1		–Std		Unit
		Min	Max	Min	Max	
Address setup time	$T_{ADDRSU}$	0.475		0.559		ns
Address hold time	$T_{ADDRHD}$	0.274		0.322		ns
Data setup time	$T_{DSU}$	0.336		0.395		ns
Data hold time	$T_{DHD}$	0.082		0.096		ns
Block select setup time	$T_{BLKSU}$	0.207		0.244		ns
Block select hold time	$T_{BLKHD}$	0.216		0.254		ns
Block select to out disable time (when pipelined register is disabled)	$T_{BLK2Q}$		1.529		1.799	ns
Block select minimum pulse width	$T_{BLKMPW}$	0.186		0.219		ns
Read enable setup time	$T_{RDESU}$	0.485		0.57		ns
Read enable hold time	$T_{RDEHD}$	0.071		0.083		ns
Pipelined read enable setup time (A_DOUT_EN, B_DOUT_EN)	$T_{RDPLESU}$	0.248		0.291		ns
Pipelined read enable hold time (A_DOUT_EN, B_DOUT_EN)	$T_{RDPLEHD}$	0.102		0.12		ns
Asynchronous reset to output propagation delay	$T_{R2Q}$		1.514		1.781	ns
Asynchronous reset removal time	$T_{RSTREM}$	0.506		0.595		ns
Asynchronous reset recovery time	$T_{RSTREC}$	0.004		0.005		ns
Asynchronous reset minimum pulse width	$T_{RSTMPW}$	0.301		0.354		ns
Pipelined register asynchronous reset removal time	$T_{PLRSTREM}$	–0.279		–0.328		ns
Pipelined register asynchronous reset recovery time	$T_{PLRSTREC}$	0.327		0.385		ns
Pipelined register asynchronous reset minimum pulse width	$T_{PLRSTMPW}$	0.282		0.332		ns
Synchronous reset setup time	$T_{SRSTSU}$	0.226		0.265		ns
Synchronous reset hold time	$T_{SRSTHD}$	0.036		0.043		ns
Write enable setup time	$T_{WESU}$	0.415		0.488		ns
Write enable hold time	$T_{WEHD}$	0.048		0.057		ns
Maximum frequency	$F_{MAX}$		400		340	MHz

The following table lists the RAM1K18 – dual-port mode for depth × width configuration 4K × 4 in worst commercial-case conditions when  $T_J = 85\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 233 • RAM1K18 – Dual-Port Mode for Depth × Width Configuration 4K × 4**

Parameter	Symbol	–1		–Std		Unit
		Min	Max	Min	Max	
Clock period	$T_{CY}$	2.5		2.941		ns
Clock minimum pulse width high	$T_{CLKMPWH}$	1.125		1.323		ns
Clock minimum pulse width low	$T_{CLKMPWL}$	1.125		1.323		ns
Pipelined clock period	$T_{PLCY}$	2.5		2.941		ns
Pipelined clock minimum pulse width high	$T_{PLCLKMPWH}$	1.125		1.323		ns

**Table 237 •  $\mu$ SRAM (RAM64x18) in 64 × 18 Mode (continued)**

Parameter	Symbol	-1		-Std		Unit
		Min	Max	Min	Max	
Write address setup time	$T_{ADDRCSU}$	0.088		0.104		ns
Write address hold time	$T_{ADDRCHD}$	0.128		0.15		ns
Write enable setup time	$T_{WECSU}$	0.397		0.467		ns
Write enable hold time	$T_{WECHD}$	-0.026		-0.03		ns
Maximum frequency	$F_{MAX}$		250		250	MHz

The following table lists the  $\mu$ SRAM in 64 × 16 mode in worst commercial-case conditions when  $T_J = 85\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 238 •  $\mu$ SRAM (RAM64x16) in 64 × 16 Mode**

Parameter	Symbol	-1		-Std		Unit
		Min	Max	Min	Max	
Read clock period	$T_{CY}$	4		4		ns
Read clock minimum pulse width high	$T_{CLKMPWH}$	1.8		1.8		ns
Read clock minimum pulse width low	$T_{CLKMPWL}$	1.8		1.8		ns
Read pipeline clock period	$T_{PLCY}$	4		4		ns
Read pipeline clock minimum pulse width high	$T_{PLCLKMPWH}$	1.8		1.8		ns
Read pipeline clock minimum pulse width low	$T_{PLCLKMPWL}$	1.8		1.8		ns
Read access time with pipeline register	$T_{CLK2Q}$		0.266		0.313	ns
Read access time without pipeline register				1.677		1.973
Read address setup time in synchronous mode	$T_{ADDRSU}$	0.301		0.354		ns
Read address setup time in asynchronous mode			1.856		2.184	
Read address hold time in synchronous mode	$T_{ADDRHD}$	0.091		0.107		ns
Read address hold time in asynchronous mode			-0.778		-0.915	
Read enable setup time	$T_{RDENSU}$	0.278		0.327		ns
Read enable hold time	$T_{RDENHD}$	0.057		0.067		ns
Read block select setup time	$T_{BLKSU}$	1.839		2.163		ns
Read block select hold time	$T_{BLKHD}$	-0.65		-0.765		ns
Read block select to out disable time (when pipelined register is disabled)	$T_{BLK2Q}$		2.036		2.396	ns
Read asynchronous reset removal time (pipelined clock)	$T_{RSTREM}$	-0.023		-0.027		ns
Read asynchronous reset removal time (non-pipelined clock)			0.046		0.054	
Read asynchronous reset recovery time (pipelined clock)	$T_{RSTREC}$	0.507		0.597		ns
Read asynchronous reset recovery time (non-pipelined clock)			0.236		0.278	
Read asynchronous reset to output propagation delay (with pipelined register enabled)	$T_{R2Q}$		0.835		0.983	ns
Read synchronous reset setup time	$T_{SRSTSU}$	0.271		0.319		ns

**Table 238 •  $\mu$ SRAM (RAM64x16) in 64 x 16 Mode (continued)**

Parameter	Symbol	-1		-Std		Unit
		Min	Max	Min	Max	
Read synchronous reset hold time	$T_{SRSTHD}$	0.061		0.071		ns
Write clock period	$T_{CCY}$	4		4		ns
Write clock minimum pulse width high	$T_{CCLKMPWH}$	1.8		1.8		ns
Write clock minimum pulse width low	$T_{CCLKMPWL}$	1.8		1.8		ns
Write block setup time	$T_{BLKCSU}$	0.404		0.476		ns
Write block hold time	$T_{BLKCHD}$	0.007		0.008		ns
Write input data setup time	$T_{DINCSU}$	0.115		0.135		ns
Write input data hold time	$T_{DINCHD}$	0.15		0.177		ns
Write address setup time	$T_{ADDRCSU}$	0.088		0.104		ns
Write address hold time	$T_{ADDRCHD}$	0.128		0.15		ns
Write enable setup time	$T_{WECSU}$	0.397		0.467		ns
Write enable hold time	$T_{WECHD}$	-0.026		-0.03		ns
Maximum frequency	$F_{MAX}$		250		250	MHz

The following table lists the  $\mu$ SRAM in 128 x 9 mode in worst commercial-case conditions when  $T_J = 85^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 239 •  $\mu$ SRAM (RAM128x9) in 128 x 9 Mode**

Parameter	Symbol	-1		-Std		Unit
		Min	Max	Min	Max	
Read clock period	$T_{CY}$	4		4		ns
Read clock minimum pulse width high	$T_{CLKMPWH}$	1.8		1.8		ns
Read clock minimum pulse width low	$T_{CLKMPWL}$	1.8		1.8		ns
Read pipeline clock period	$T_{PLCY}$	4		4		ns
Read pipeline clock minimum pulse width high	$T_{PLCLKMPWH}$	1.8		1.8		ns
Read pipeline clock minimum pulse width low	$T_{PLCLKMPWL}$	1.8		1.8		ns
Read access time with pipeline register	$T_{CLK2Q}$		0.266		0.313	ns
Read access time without pipeline register				1.677		1.973
Read address setup time in synchronous mode	$T_{ADDRSU}$	0.301		0.354		ns
Read address setup time in asynchronous mode			1.856		2.184	
Read address hold time in synchronous mode	$T_{ADDRHD}$	0.091		0.107		ns
Read address hold time in asynchronous mode			-0.778		-0.915	
Read enable setup time	$T_{RDENSU}$	0.278		0.327		ns
Read enable hold time	$T_{RDENHD}$	0.057		0.067		ns
Read block select setup time	$T_{BLKSU}$	1.839		2.163		ns
Read block select hold time	$T_{BLKHD}$	-0.65		-0.765		ns
Read block select to out disable time (when pipelined register is disabled)	$T_{BLK2Q}$		2.036		2.396	ns

**Table 248 • 2 Step IAP Programming (eNVM Only)**

<b>M2S/M2GL</b>					
<b>Device</b>	<b>Image size Bytes</b>	<b>Authenticate</b>	<b>Program</b>	<b>Verify</b>	<b>Unit</b>
005	137536	2	37	5	Sec
010	274816	4	76	11	Sec
025	274816	4	78	10	Sec
050	278528	3	85	9	Sec
060	268480	5	76	22	Sec
090	544496	10	152	43	Sec
150	544496	10	153	44	Sec

**Table 249 • 2 Step IAP Programming (Fabric and eNVM)**

<b>M2S/M2GL</b>					
<b>Device</b>	<b>Image size Bytes</b>	<b>Authenticate</b>	<b>Program</b>	<b>Verify</b>	<b>Unit</b>
005	439296	6	56	11	Sec
010	842688	11	100	21	Sec
025	1497408	19	113	32	Sec
050	2695168	32	136	48	Sec
060	2686464	43	137	70	Sec
090	4190208	68	236	115	Sec
150	6682768	109	286	162	Sec

**Table 250 • SmartFusion2 Cortex-M3 ISP Programming (Fabric Only)**

<b>M2S/M2GL</b>					
<b>Device</b>	<b>Image size Bytes</b>	<b>Authenticate</b>	<b>Program</b>	<b>Verify</b>	<b>Unit</b>
005	302672	6	19	8	Sec
010	568784	10	26	14	Sec
025	1223504	21	39	29	Sec
050	2424832	39	60	50	Sec
060	2418896	44	65	54	Sec
090	3645968	66	90	79	Sec
150	6139184	108	140	128	Sec

**Table 251 • SmartFusion2 Cortex-M3 ISP Programming (eNVM Only)**

<b>M2S/M2GL</b>					
<b>Device</b>	<b>Image size Bytes</b>	<b>Authenticate</b>	<b>Program</b>	<b>Verify</b>	<b>Unit</b>
005	137536	3	42	4	Sec
010	274816	4	82	7	Sec
025	274816	4	82	8	Sec
050	278528	4	80	8	Sec
060	268480	6	80	8	Sec
090	544496	10	157	15	Sec



The following table lists the programming times in worst-case conditions when  $T_J = 100\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ . External SPI flash part# AT25DF641-s3H is used during this measurement.

**Table 256 • JTAG Programming (Fabric Only)**

M2S/M2GL Device	Image size		Verify	Unit
	Bytes	Program		
005	302672	44	10	Sec
010	568784	50	18	Sec
025	1223504	73	26	Sec
050	2424832	88	54	Sec
060	2418896	99	54	Sec
090	3645968	135	126	Sec
150	6139184	177	193	Sec

**Table 257 • JTAG Programming (eNVM Only)**

M2S/M2GL Device	Image size		Verify	Unit
	Bytes	Program		
005	137536	61	4	Sec
010	274816	100	9	Sec
025	274816	100	9	Sec
050	2,78,528	106	8	Sec
060	268480	98	8	Sec
090	544496	176	15	Sec
150	544496	177	15	Sec

**Table 258 • JTAG Programming (Fabric and eNVM)**

M2S/M2GL Device	Image size		Verify	Unit
	Bytes	Program		
005	439296	71	11	Sec
010	842688	129	20	Sec
025	1497408	142	35	Sec
050	2695168	184	59	Sec
060	2686464	180	70	Sec
090	4190208	288	147	Sec
150	6682768	338	231	Sec

## 2.3.14 Math Block Timing Characteristics

The fundamental building block in any digital signal processing algorithm is the multiply-accumulate function. Each IGLOO2 and SmartFusion2 SoC math block supports 18×18 signed multiplication, dot product, and built-in addition, subtraction, and accumulation units to combine multiplication results efficiently. The following table lists the math blocks with all registers used in worst commercial-case conditions when  $T_J = 85\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 268 • Math Blocks with all Registers Used**

Parameter	Symbol	-1		-Std		Unit
		Min	Max	Min	Max	
Input, control register setup time	$T_{MISU}$	0.149		0.176		ns
Input, control register hold time	$T_{MIHD}$	1.68		1.976		ns
CDIN input setup time	$T_{MOCDINSU}$	0.185		0.218		ns
CDIN input hold time	$T_{MOCDINHHD}$	0.08		0.094		ns
Synchronous reset/enable setup time	$T_{MSRSTENSU}$	-0.419		-0.493		ns
Synchronous reset/enable hold time	$T_{MSRSTENHD}$	0.011		0.013		ns
Asynchronous reset removal time	$T_{MARSTREM}$	0		0		ns
Asynchronous reset recovery time	$T_{MARSTREC}$	0.088		0.104		ns
Output register clock to out delay	$T_{MOCQ}$		0.232		0.273	ns
CLK minimum period	$T_{MCLKMP}$	2.245		2.641		ns

The following table lists the math blocks with input bypassed and output registers used in worst commercial-case conditions when  $T_J = 85\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

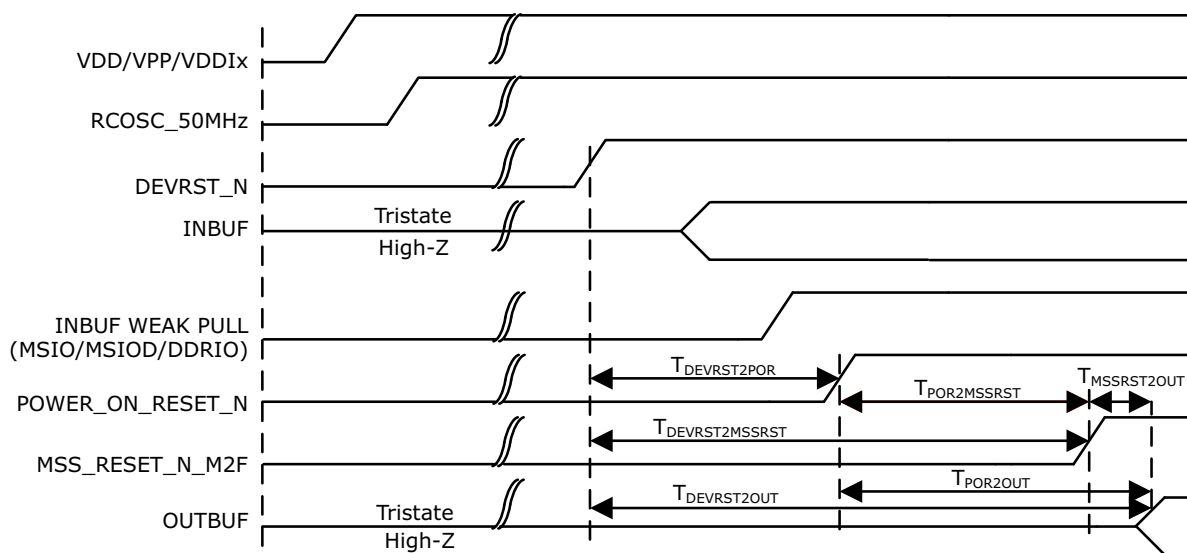
**Table 269 • Math Block with Input Bypassed and Output Registers Used**

Parameter	Symbol	-1		-Std		Unit
		Min	Max	Min	Max	
Output register setup time	$T_{MOSU}$	2.294		2.699		ns
Output register hold time	$T_{MOHD}$	1.68		1.976		ns
CDIN input setup time	$T_{MOCDINSU}$	0.115		0.136		ns
CDIN input hold time	$T_{MOCDINHHD}$	-0.444		-0.522		ns
Synchronous reset/enable setup time	$T_{MSRSTENSU}$	-0.419		-0.493		ns
Synchronous reset/enable hold time	$T_{MSRSTENHD}$	0.011		0.013		ns
Asynchronous reset removal time	$T_{MARSTREM}$	0		0		ns
Asynchronous reset recovery time	$T_{MARSTREC}$	0.014		0.017		ns
Output register clock to out delay	$T_{MOCQ}$		0.232		0.273	ns
CLK minimum period	$T_{MCLKMP}$	2.179		2.563		ns

**Table 291 • DEVRST\_N to Functional Times for SmartFusion2 (continued)**

Symbol	From	To	Description	Maximum Power-up to Functional Time for SmartFusion2 (uS)						
				005	010	025	050	060	090	150
$T_{DEVRST2POR}$	DEVRST_N	POWER_ON_RESET_N	$V_{DD}$ at its minimum threshold level to fabric	233	289	216	213	237	234	219
$T_{DEVRST2MSSRST}$	DEVRST_N	MSS_RESET_N_M2F	$V_{DD}$ at its minimum threshold level to MSS	702	765	712	688	636	630	866
$T_{DEVRST2WPU}$	DEVRST_N	DDRIO Inbuf weak pull	DEVRST_N to Inbuf weak pull	208	202	197	193	216	215	215
	DEVRST_N	MSIO Inbuf weak pull	DEVRST_N to Inbuf weak pull	208	202	197	193	216	215	215
	DEVRST_N	MSIOD Inbuf weak pull	DEVRST_N to Inbuf weak pull	208	202	197	193	216	215	215

**Figure 19 • DEVRST\_N to Functional Timing Diagram for SmartFusion2**



The following table lists the IGLOO2 DEVRST\_N to functional times in worst-case industrial conditions when  $T_J = 100\text{ }^\circ\text{C}$ ,  $V_{DD} = 1.14\text{ V}$ .

**Table 292 • DEVRST\_N to Functional Times for IGLOO2**

Symbol	From	To	Description	Maximum Power-up to Functional Time for IGLOO2 (uS)						
				005	010	025	050	060	090	150
$T_{POR2OUT}$	POWER_ON_RESET_N	Output available at I/O	Fabric to output	114	116	113	113	115	115	114
$T_{DEVRST2OUT}$	DEVRST_N	Output available at I/O	$V_{DD}$ at its minimum threshold level to output	314	353	314	307	343	341	341
$T_{DEVRST2POR}$	DEVRST_N	POWER_ON_RESET_N	$V_{DD}$ at its minimum threshold level to fabric	200	238	201	195	230	229	227
$T_{DEVRST2WPU}$	DEVRST_N	DDRIO Inbuf weak pull	DEVRST_N to Inbuf weak pull	208	202	197	193	216	215	215
	DEVRST_N	MSIO Inbuf weak pull	DEVRST_N to Inbuf weak pull	208	202	197	193	216	215	215
	DEVRST_N	MSIOD Inbuf weak pull	DEVRST_N to Inbuf weak pull	208	202	197	193	216	215	215

**Table 303 • I2C Characteristics (continued)**

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Maximum data rate	$D_{MAX}$			400	Kbps	Fast mode
				100	Kbps	Standard mode
Pulse width of spikes which must be suppressed by the input filter	$T_{FILT}$		50		ns	Fast mode

1. These values are provided for MSIO Bank–LVTTTL 8 mA Low Drive at 25 °C, typical conditions. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the SoC Products Group website: <http://www.microsemi.com/soc/download/ibis/default.aspx>.
2. These maximum values are provided for information only. Minimum output buffer resistance values depend on  $V_{DDIX}$ , drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the SoC Products Group website: <http://www.microsemi.com/soc/download/ibis/default.aspx>.
3.  $R(PULL-DOWN-MAX) = (VOLspec)/IOLspec$ .
4.  $R(PULL-UP-MAX) = (VDDImax-VOHspec)/IOHspec$ .

The following table lists the I<sup>2</sup>C switching characteristics in worst-case industrial conditions when  $T_J = 100\text{ °C}$ ,  $V_{DD} = 1.14\text{ V}$

**Table 304 • I2C Switching Characteristics**

Parameter	Symbol	-1		Unit
		Min	Min	
Low period of I2C_x_SCL	$T_{LOW}$	1	1	PCLK cycles
High period of I2C_x_SCL	$T_{HIGH}$	1	1	PCLK cycles
START hold time	$T_{HD;STA}$	1	1	PCLK cycles
START setup time	$T_{SU;STA}$	1	1	PCLK cycles
DATA hold time	$T_{HD;DAT}$	1	1	PCLK cycles
DATA setup time	$T_{SU;DAT}$	1	1	PCLK cycles
STOP setup time	$T_{SU;STO}$	1	1	PCLK cycles

**Figure 21 • I<sup>2</sup>C Timing Parameter Definition**

